

PHOTOTRANSISTOR

BPW 40

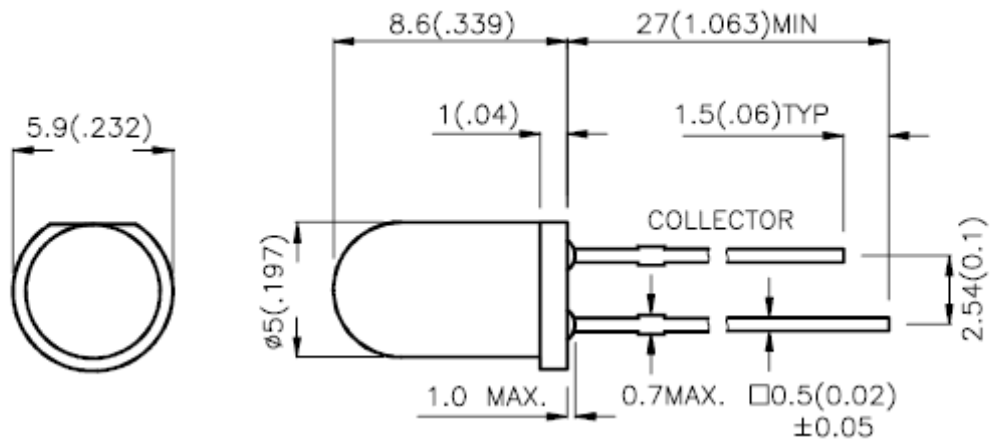
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE BPW 40 INFRARED EMITTING LED LAMP.
- WATER CLEAR LENS

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All Dimensions are in millimeters (inches).
2. Tolerance is ± 0.25 (0.01") unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Electrical / Optical Characteristics at T_A=25°C

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V _{BR CEO}	Collector-to-Emitter Breakdown Voltage	30	-	-	V	I _C =100μA E _e =0mW/cm ²
V _{BR ECO}	Emitter-to-Collector Breakdown Voltage	5	-	-	V	I _E =100μA E _e =0mW/cm ²
V _{CE (SAT)}	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	I _C =2mA E _e =20mW/cm ²
I _{CEO}	Collector Dark Current	-	-	100	nA	V _{CE} =10V E _e =0mW/cm ²
T _R	Rise Time (10% to 90%)	-	3	-	us	V _{CE} =5V I _C =1mA R _L =1000Ω
T _F	Fall Time (90% to 10%)	-	3	-	us	
I _(ON)	On State Collector Current	0.1	0.5	-	mA	V _{CE} =5V E _e =1mW/cm ² λ=940nm

Absolute Maximum Ratings at T_A=25°C

Parameter	Maximum Rating
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power Dissipation at (or below) 25°C Free Air Temperature	100mW
Operating Temperature Range	-40°C ~ +85°C
Storage Temperature Range	-40°C ~ +85°C
Lead soldering Temperature (>5mm for 5sec)	260°C